

Product data sheet

1. General description

PNP low V_{CEsat} Breakthrough In Small Signal (BISS) transistor in a leadless ultra small DFN1010D-3 (SOT1215) Surface-Mounted Device (SMD) plastic package with visible and solderable side pads.

NPN complement: PBSS4230QA.

2. Features and benefits

- Very low collector-emitter saturation voltage V_{CEsat}
- High collector current capability ${\sf I}_{\sf C}$ and ${\sf I}_{\sf CM}$
- High collector current gain h_{FE} at high I_C
- High energy efficiency due to less heat generation
- Reduced Printed-Circuit Board (PCB) area requirements
- Solderable side pads
- AEC-Q101 qualified

3. Applications

- Loadswitch
- Battery-driven devices
- Power management
- Charging circuits
- Power switches (e.g. motors, fans)

4. Quick reference data

Table 1. Quie	ck reference data					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V _{CEO}	collector-emitter voltage	open base	-	-	-30	V
I _C	collector current		-	-	-2	А
I _{CM}	peak collector current	t _p ≤ 1 ms; pulsed	-	-	-3	А
R _{CEsat}	collector-emitter saturation resistance	I_C = -1 A; I_B = -100 mA; pulsed; t_p ≤ 300 μs; δ ≤ 0.02 ; T_{amb} = 25 °C	-	120	180	mΩ

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5. Pinning information

Table 2.	Pinning	information		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	В	base		С
2	Е	emitter		в-
3	С	collector	4 3	۲۹ ۲
4	С	collector		sym132
			Transparent top view DFN1010D-3 (SOT1215)	

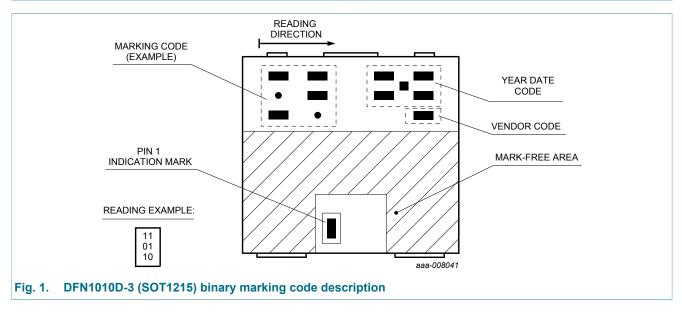
6. Ordering information

Table 3. Ordering information						
Type number	Package					
	Name	Description	Version			
PBSS5230QA	DFN1010D-3	plastic thermal enhanced ultra thin small outline package; no leads; 3 terminals	SOT1215			

7. Marking

Table 4. Marking codes

Type number	Marking code
PBSS5230QA	00 00 10



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8. Limiting values

Table 5.Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V _{CBO}	collector-base voltage	open emitter		-	-30	V
V _{CEO}	collector-emitter voltage	open base		-	-30	V
V _{EBO}	emitter-base voltage	open collector		-	-7	V
I _C	collector current			-	-2	А
I _{CM}	peak collector current	$t_p \le 1 ms; pulsed$		-	-3	А
I _B	base current			-	-0.3	А
I _{BM}	peak base current	$t_p \le 1 ms; pulsed$		-	-1	А
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C	[1]	-	325	mW
			[2]	-	600	mW
			[3]	-	740	mW
			[4]	-	540	mW
			[5]	-	1000	mW
Tj	junction temperature			-	150	°C
T _{amb}	ambient temperature			-55	150	°C
T _{stg}	storage temperature			-65	150	°C

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated mounting pad for collector 1 cm².

[3] Device mounted on an FR4 PCB, single-sided copper, tin-plated mounting pad for collector 6 cm².

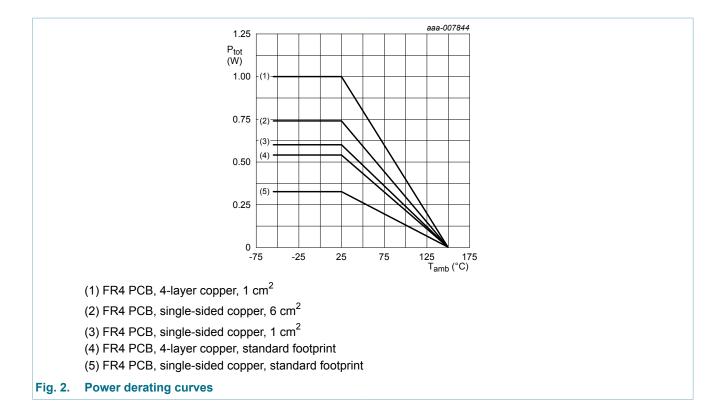
[4] Device mounted on an FR4 PCB, 4-layer copper, tin-plated and standard footprint.

^[5] Device mounted on an FR4 PCB, 4-layer copper, tin-plated mounting pad for collector 1 cm².

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9. Thermal characteristics

Table 6. T	hermal characteristics						
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
fror	thermal resistance	in free air	[1]	-	-	385	K/W
	from junction to ambient		[2]	-	-	209	K/W
	ampient		[3]	-	-	169	K/W
			[4]	-	-	232	K/W
			[5]	-	-	125	K/W

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

^[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated mounting pad for collector 1 cm².

[3] Device mounted on an FR4 PCB, single-sided copper, tin-plated mounting pad for collector 6 cm².

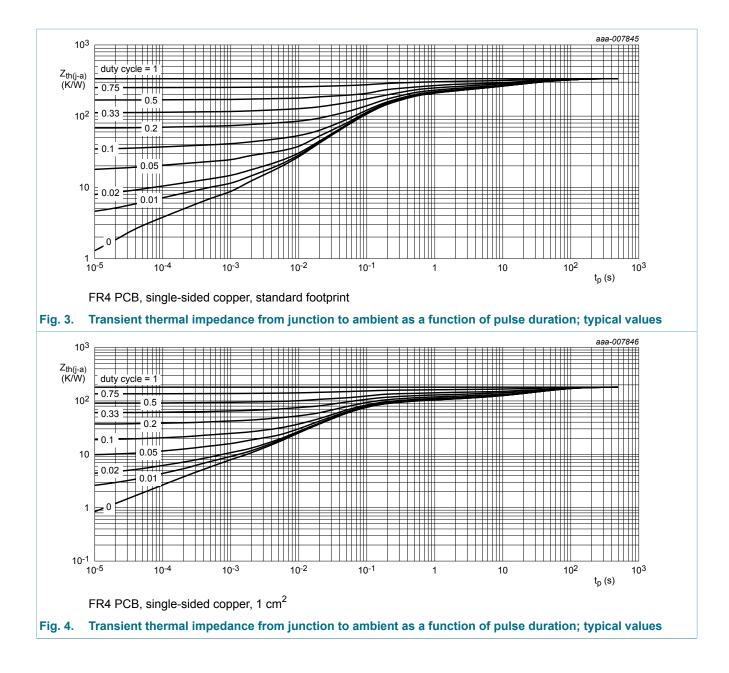
[4] Device mounted on an FR4 PCB, 4-layer copper, tin-plated and standard footprint.

[5] Device mounted on an FR4 PCB, 4-layer copper, tin-plated mounting pad for collector 1 cm².

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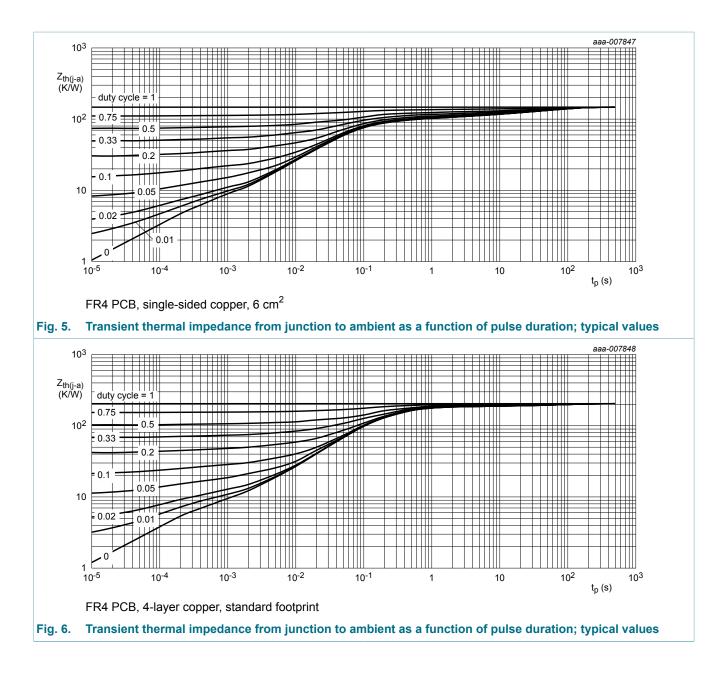


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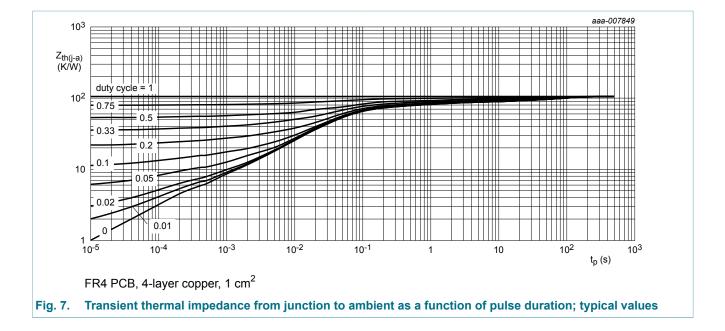
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10. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
I _{CBO}	collector-base cut-off	V _{CB} = -24 V; I _E = 0 A; T _{amb} = 25 °C	-	-	-100	nA
	current	V_{CB} = -24 V; I _E = 0 A; T _j = 150 °C	-	-	-50	μA
I _{CES}	collector-emitter cut-off current	V_{CE} = -24 V; V_{BE} = 0 V; T_{amb} = 25 °C	-	-	-100	nA
I _{EBO}	emitter-base cut-off current	V _{EB} = -5 V; I _C = 0 A; T _{amb} = 25 °C	-	-	-100	nA
h _{FE}	DC current gain	$V_{CE} = -2 \text{ V; } I_C = -100 \text{ mA; } t_p \le 300 \mu\text{s;}$ $\delta \le 0.02 \text{ ; } T_{amb} = 25 \text{ °C; } \text{pulsed}$	250	425	-	
		$\label{eq:VCE} \begin{array}{l} V_{CE} = -2 \; V; \; I_{C} = -500 \; \text{mA}; \; t_{p} \leq 300 \; \mu \text{s}; \\ \delta \leq 0.02 \; ; \; T_{amb} = 25 \; ^{\circ}\text{C}; \; \text{pulsed} \end{array}$	180	295	-	
		$\begin{split} V_{CE} &= -2 \text{ V}; \text{ I}_{C} = -1 \text{ A}; \text{t}_{p} \leq 300 \mu\text{s}; \\ \delta &\leq 0.02 ; \text{T}_{amb} = 25 ^\circ\text{C}; \text{ pulsed} \end{split}$	130	200	-	
		V_{CE} = -2 V; I _C = -2 A; t _p ≤ 300 µs; $\delta \le 0.02$; T _{amb} = 25 °C; pulsed	60	95	-	
V _{CEsat}	collector-emitter saturation voltage	$I_{C} = -500 \text{ mA}; I_{B} = -50 \text{ mA}; t_{p} \le 300 \mu\text{s};$ $\delta \le 0.02 \text{ ; } T_{amb} = 25 ^{\circ}\text{C}$	-	-70	-100	mV
		I_C = -1 A; I_B = -50 mA; t_p ≤ 300 μs; δ ≤ 0.02 ; T_{amb} = 25 °C	-	-140	-210	mV
		I _C = -1 A; I _B = -100 mA; pulsed; t _p ≤ 300 μs; δ ≤ 0.02 ; T _{amb} = 25 °C	-	-120	-180	mV

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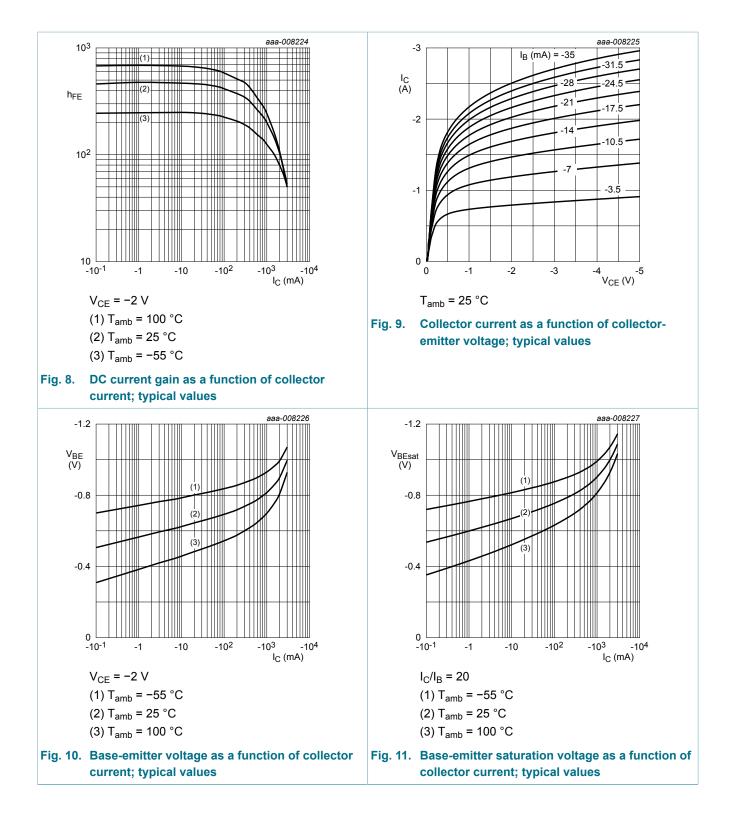
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Symbol	Parameter	Conditions	IV	lin	Тур	Max	Unit
		$\begin{split} I_{C} &= -2 \text{ A}; I_{B} = -100 \text{ mA}; \text{ pulsed}; \\ t_{p} &\leq 300 \mu\text{s}; \delta \leq 0.02 ; T_{amb} = 25 ^{\circ}\text{C} \end{split}$	-		-275	-410	mV
		I_{C} = -2 A; I_{B} = -200 mA; pulsed; $t_{p} \le 300 \ \mu$ s; δ ≤ 0.02 ; T_{amb} = 25 °C	-		-220	-330	mV
R _{CEsat}	collector-emitter saturation resistance	I_{C} = -1 A; I_{B} = -100 mA; pulsed; $t_{p} \le 300 \ \mu$ s; δ ≤ 0.02 ; T_{amb} = 25 °C	-		120	180	mΩ
V _{BEsat}	base-emitter saturation voltage	$\begin{split} I_C &= -500 \text{ mA; } I_B = -50 \text{ mA; pulsed;} \\ t_p &\leq 300 \mu\text{s; } \delta \leq 0.02 \text{ ; } T_{\text{amb}} = 25 ^\circ\text{C} \end{split}$	-		-0.86	-1	V
		I_{C} = -1 A; I_{B} = -50 mA; pulsed; $t_{p} \le 300 \ \mu$ s; δ ≤ 0.02 ; T_{amb} = 25 °C	-		-0.89	-1.05	V
		I_{C} = -2 A; I_{B} = -100 mA; pulsed; $t_{p} \le 300 \ \mu$ s; δ ≤ 0.02 ; T_{amb} = 25 °C	-		-0.98	-1.15	V
		I_{C} = -2 A; I_{B} = -200 mA; pulsed; $t_{p} \le 300 \ \mu$ s; δ ≤ 0.02 ; T_{amb} = 25 °C	-		-1.02	-1.2	V
V _{BEon}	base-emitter turn-on voltage	$\label{eq:VcE} \begin{array}{l} V_{CE} \texttt{=} \texttt{-2} \; V \texttt{;} \; I_{C} \texttt{=} \texttt{-0.5} \; A \texttt{;} \; \texttt{pulsed} \texttt{;} \\ t_{p} \texttt{\leq} \texttt{300} \; \mu \texttt{s} \texttt{;} \; \delta \texttt{\leq} \texttt{0.02} \texttt{;} \; T_{amb} \texttt{=} \texttt{25} \; ^{\circ} C \end{array}$	-		-0.77	-0.9	V
t _d	delay time	V_{CC} = -10 V; I_{C} = -0.5 A; I_{Bon} = -25 mA;	-		10	-	ns
t _r	rise time	I _{Boff} = 25 mA; T _{amb} = 25 °C	-		30	-	ns
t _{on}	turn-on time		-		40	-	ns
t _s	storage time		-		270	-	ns
t _f	fall time		-		45	-	ns
t _{off}	turn-off time		-		315	-	ns
f _T	transition frequency	V_{CE} = -10 V; I _C = -50 mA; f = 100 MHz; T _{amb} = 25 °C	1	120	170	-	MHz
C _c	collector capacitance	V _{CB} = -10 V; I _E = 0 A; i _e = 0 A; f = 1 MHz; T _{amb} = 25 °C	-		14	16	pF

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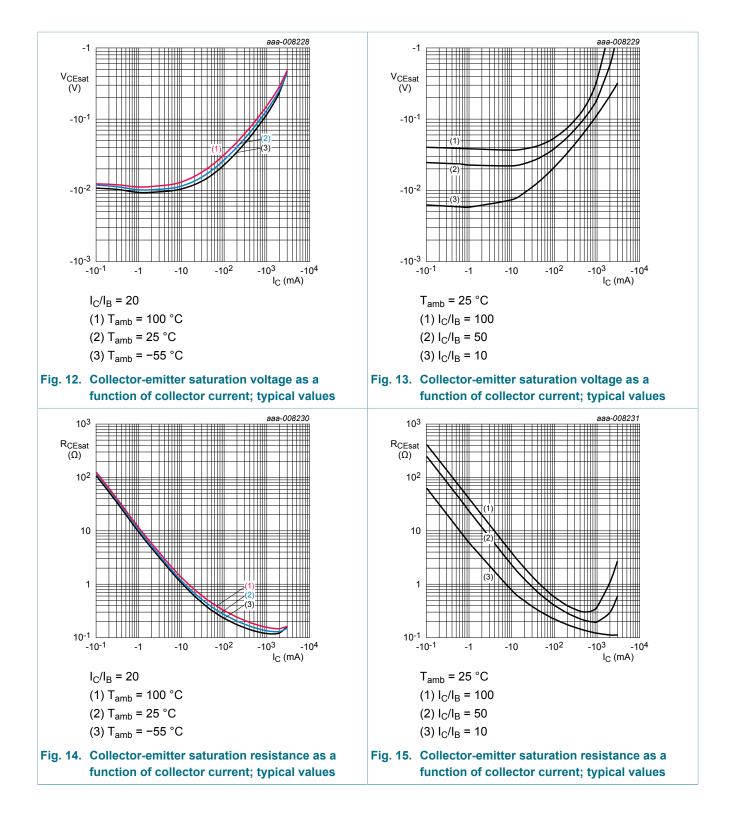


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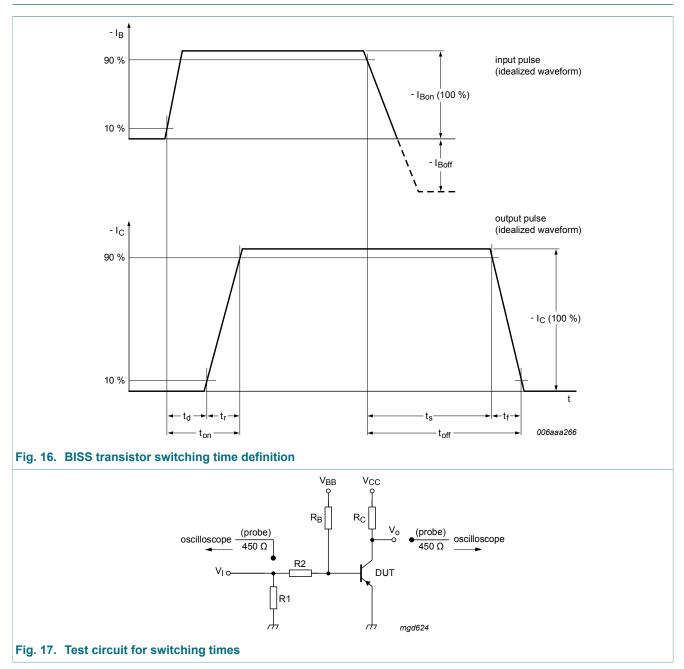
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11. Test information

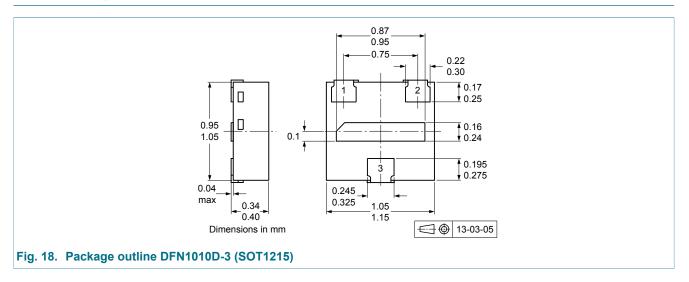


This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard *Q101* - *Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

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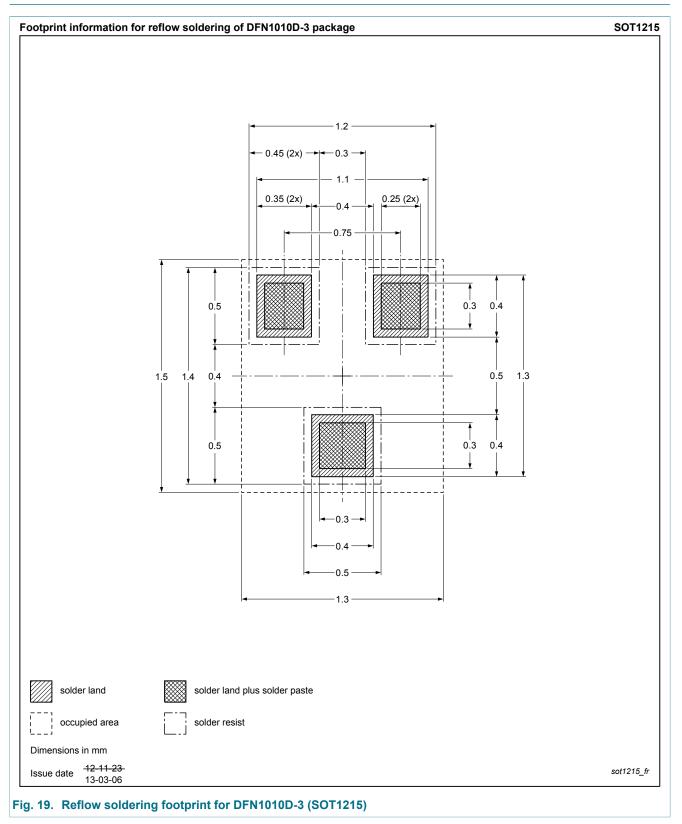
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12. Package outline



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13. Soldering



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14. Revision history

Table 8. Revision his	story			
Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
PBSS5230QA v.1	20130823	Product data sheet	-	-

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15. Legal information

15.1 Data sheet status

Document status [1][2]	Product status [<u>3]</u>	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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